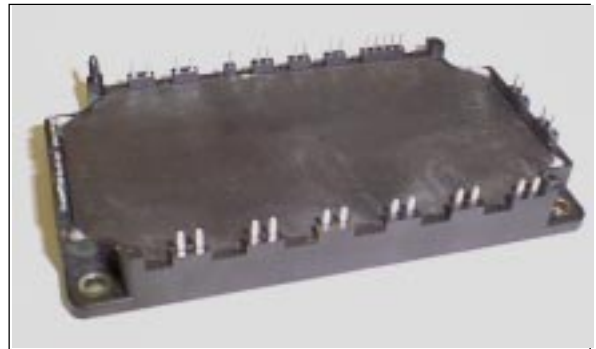


PIM/Built-in converter with thyristor and brake (S series) 1200V / 35A / PIM



■ Features

- Low $V_{CE(sat)}$
- Compact Package
- P.C. Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

■ Maximum ratings and characteristics

● Absolute maximum ratings ($T_c=25^\circ\text{C}$ unless without specified)

Item	Symbol	Condition	Rating	Unit	
Inverter	Collector-Emitter voltage	V_{CES}	1200	V	
	Gate-Emitter voltage	V_{GES}	± 20	V	
	Collector current	I_c	Continuous	$T_c=25^\circ\text{C}$ 50 $T_c=80^\circ\text{C}$ 35	A
		I_{CP}	1ms	$T_c=25^\circ\text{C}$ 100 $T_c=80^\circ\text{C}$ 70	A
		$-I_c$		35	A
	Collector power dissipation	P_c	1 device	240	W
Brake	Collector-Emitter voltage	V_{CES}	1200	V	
	Gate-Emitter voltage	V_{GES}	± 20	V	
	Collector current	I_c	Continuous	$T_c=25^\circ\text{C}$ 35 $T_c=80^\circ\text{C}$ 25	A
		I_{CP}	1ms	$T_c=25^\circ\text{C}$ 70 $T_c=80^\circ\text{C}$ 50	A
	Collector power dissipation	P_c	1 device	180	W
	Repetitive peak reverse voltage(Diode)	V_{RRM}		1200	V
Thyristor	Repetitive peak off-state voltage	V_{DRM}	1600	V	
	Repetitive peak reverse voltage	V_{RRM}	1600	V	
	Average on-state current	$I_{T(AV)}$	50Hz/60Hz sine wave	35	A
	Surge On-state current (Non-Repetitive)	I_{TSM}	$T_j=125^\circ\text{C}$, 10ms half sine wave	390	A
	Junction temperature	T_{jw}		125	$^\circ\text{C}$
Converter	Repetitive peak reverse voltage	V_{RRM}	1600	V	
	Average output current	I_b	50Hz/60Hz sine wave	35	A
	Surge current (Non-Repetitive)	I_{FSM}	$T_j=150^\circ\text{C}$, 10ms	360	A
	I^2t (Non-Repetitive)	I^2t	half sine wave	648	A^2s
Junction temperature (except Thyristor)	T_j		+150	$^\circ\text{C}$	
Storage temperature	T_{stg}		-40 to +125	$^\circ\text{C}$	
Isolation between terminal and copper base *2 voltage between thermistor and others *3	V_{iso}	AC : 1 minute	AC 2500	V	
			AC 2500	V	
Mounting screw torque			1.7 *1	N·m	

*1 Recommendable value : 1.3 to 1.7 N·m (M4)

*2 All terminals should be connected together when isolation test will be done.

*3 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 26 should be connected together and shorted to copper base.

● Electrical characteristics (T_j=25°C unless otherwise specified)

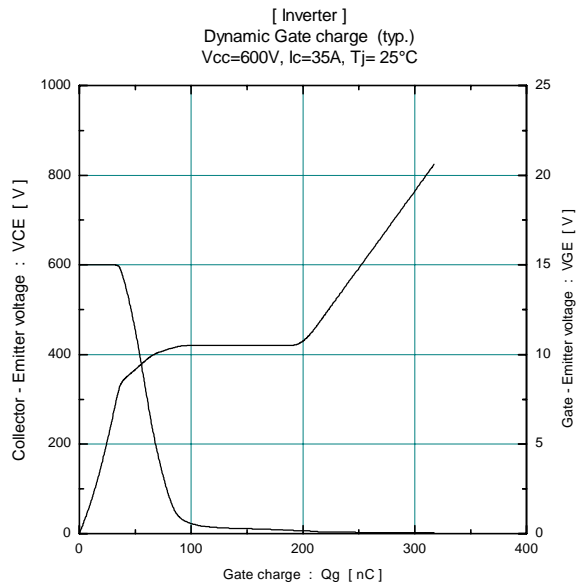
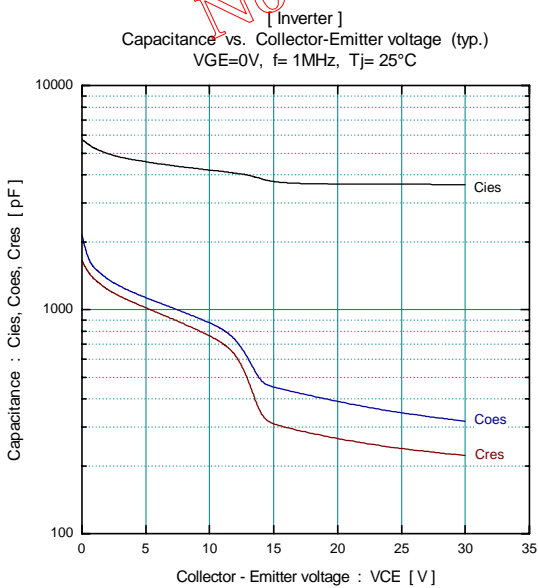
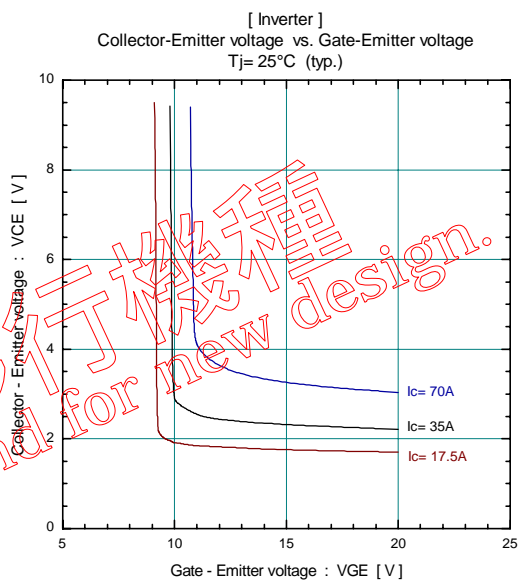
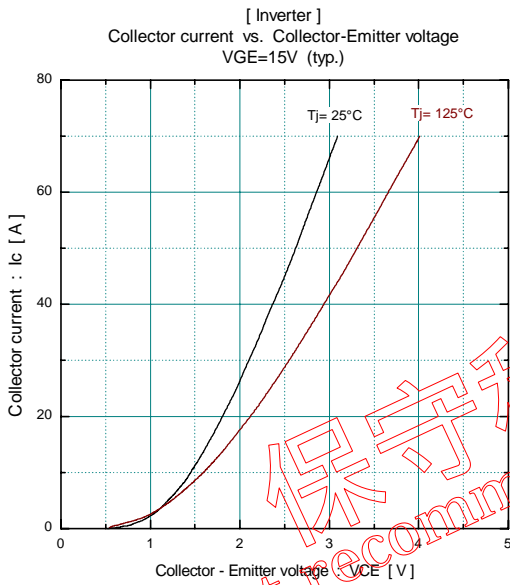
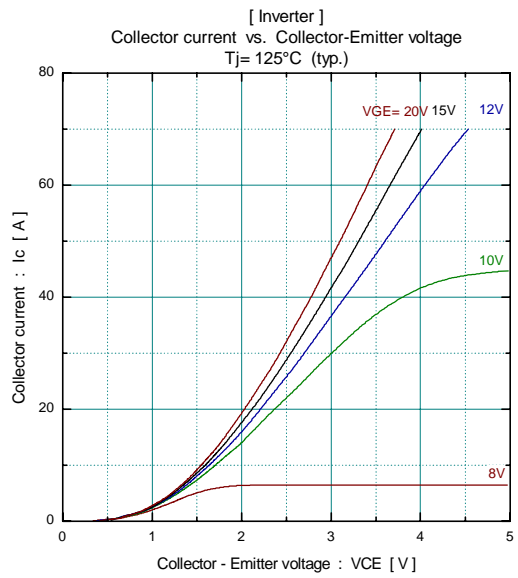
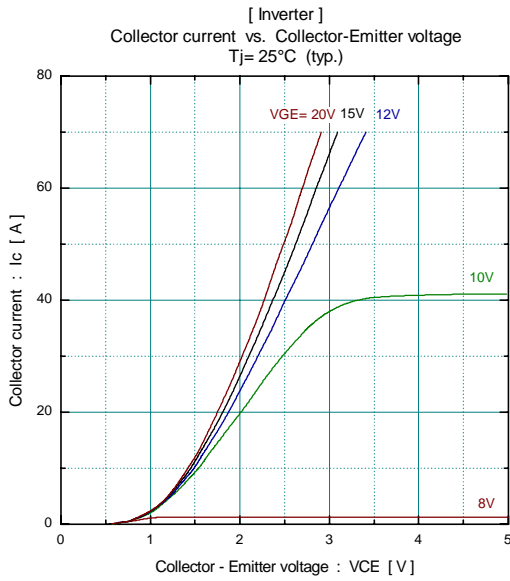
Item	Symbol	Condition	Characteristics			Unit		
			Min.	Typ.	Max.			
Inverter	Zero gate voltage collector current	ICES	V _{CE} =1200V, V _{GE} =0V		200	μA		
	Gate-Emitter leakage current	IGES	V _{CE} =0V, V _{GE} =±20V		200	nA		
	Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} =20V, I _c =35mA		5.5	7.2	8.5	V
	Collector-Emitter saturation voltage	V _{CE(sat)}	V _{GE} =15V, I _c =35A	chip	2.1		V	
				terminal	2.25	2.7		
	Input capacitance	C _{ies}	V _{GE} =0V, V _{CE} =10V, f=1MHz		4200		pF	
	Turn-on time	t _{on}	V _{CC} =600V I _c =35A		0.35	1.2	μs	
					0.25	0.6		
	Turn-off	t _{off}	V _{GE} =±15V R _G =33Ω		0.45	1.0		
					0.08	0.3		
Forward on voltage	V _F	I _F =35A	chip	2.3		V		
			terminal	2.45	3.3			
Reverse recovery time of FRD	t _{rr}	I _F =35A			350	ns		
Brake	Zero gate voltage collector current	ICES	V _{CEs} =1200V, V _{GE} =0V		200	μA		
	Gate-Emitter leakage current	IGES	V _{CE} =0V, V _{GE} =±20V		200	nA		
	Collector-Emitter saturation voltage	V _{CE(sat)}	I _c =25A, V _{GE} =15V	chip	2.1		V	
				terminal	2.25	2.7		
	Turn-on time	t _{on}	V _{CC} =600V I _c =25A		0.35	1.2	μs	
					0.25	0.6		
	Turn-off time	t _{off}	V _{GE} =±15V R _G =51Ω		0.45	1.0		
					0.08	0.3		
	Reverse current	I _{RRM}	V _R =1200V			200	μA	
	off-state current	I _{DM}	V _{DM} =1600V			1.0	mA	
Reverse current	I _{RRM}	V _{RM} =1600V			1.0	mA		
Thyristor	Gate trigger current	I _{GT}	V _D =6V, I _T =1A		100	mA		
	Gate trigger voltage	V _{GT}	V _D =6V, I _T =1A		2.5	V		
	On-state voltage	V _{TM}	I _{TM} =35A	chip	1.1	1.2	V	
terminal				1.2				
Converter	Forward on voltage	V _{FM}	I _F =35A	chip	1.1	V		
				terminal	1.2		1.5	
Reverse current	I _{RRM}	V _R =1600V			200	μA		
Thermistor	Resistance	R	T=25°C	5000		Ω		
			T=100°C	465	495		520	
B value	B	T=25/50°C	3305	3375	3450	K		

● Thermal resistance Characteristics

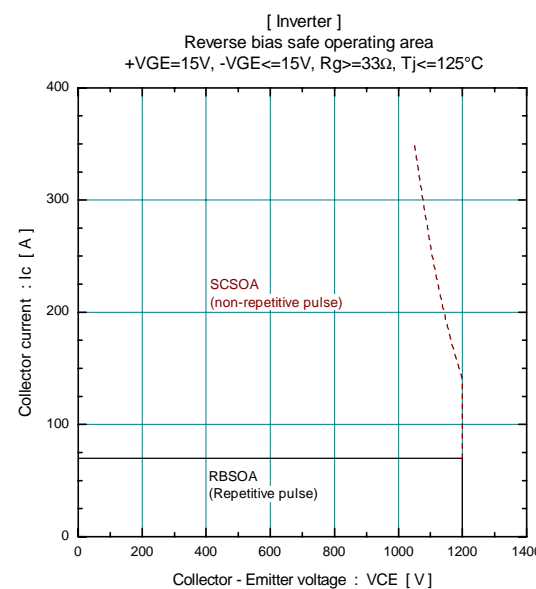
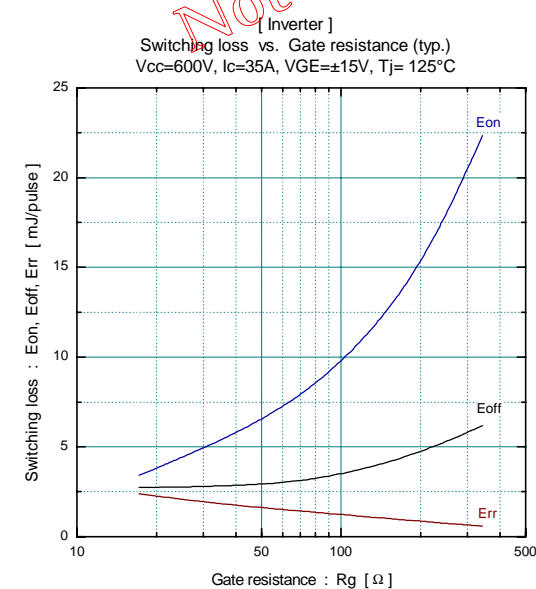
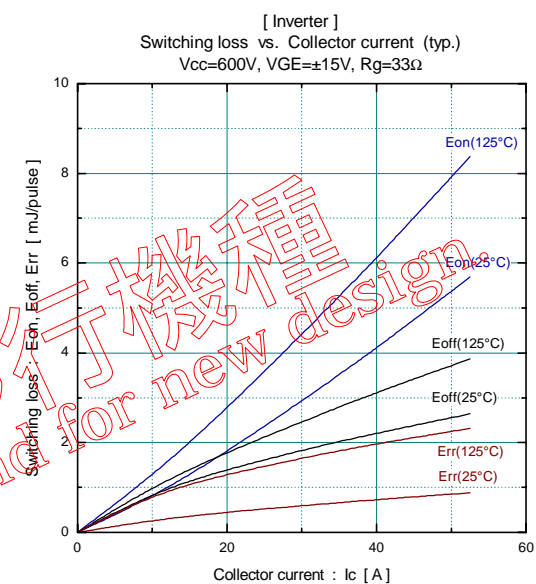
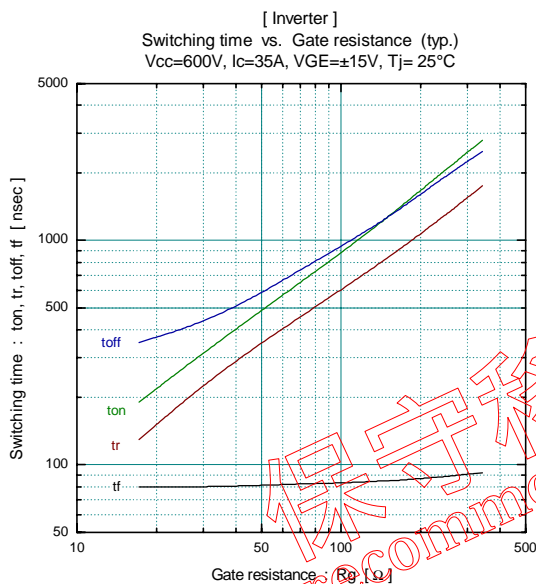
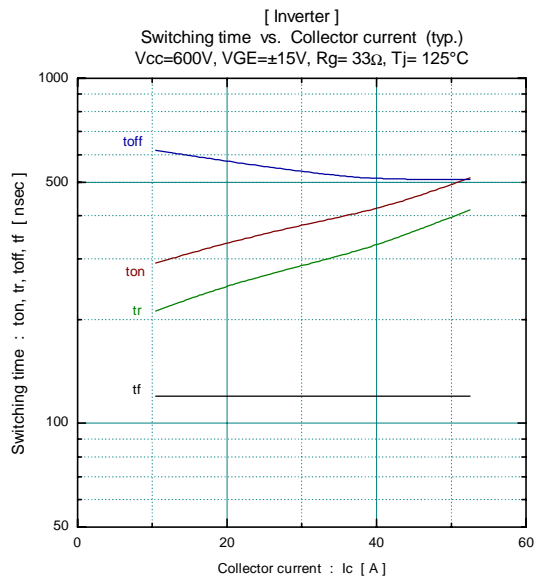
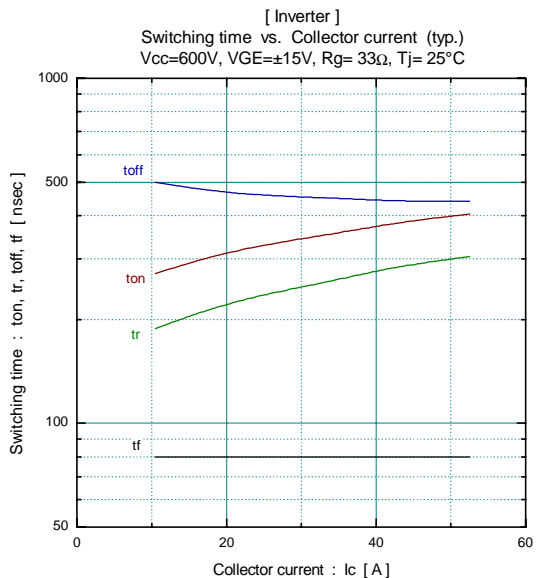
Item	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance (1 device)	R _{th(j-c)}	Inverter IGBT			0.52	°C/W
		Inverter FWD			0.90	
		Brake IGBT			0.69	
		Thyristor			1.00	
		Converter Diode			0.75	
Contact thermal resistance *	R _{th(c-f)}	With thermal compound		0.05		

* This is the value which is defined mounting on the additional cooling fin with thermal compound

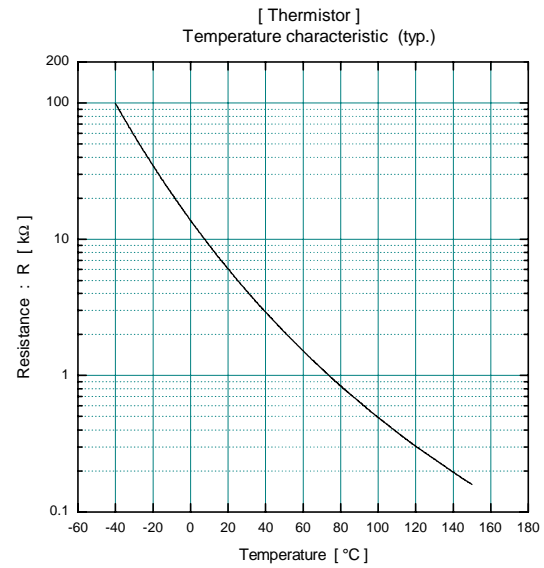
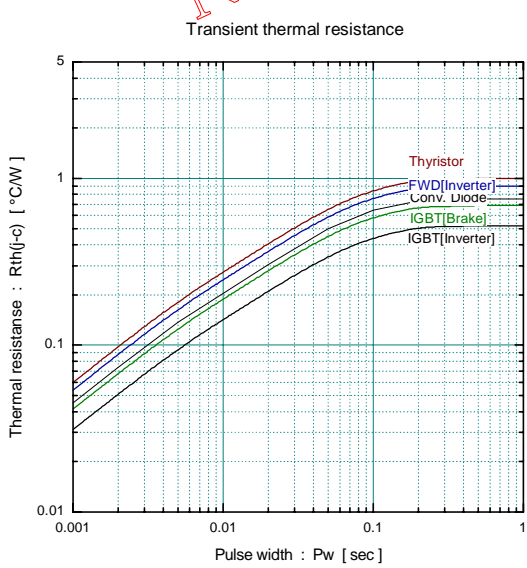
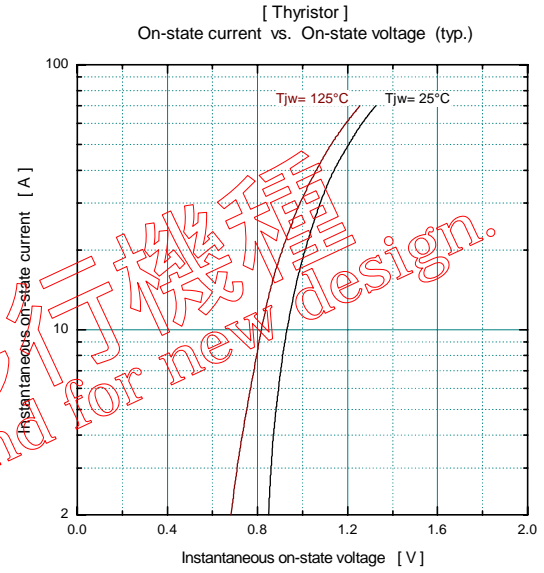
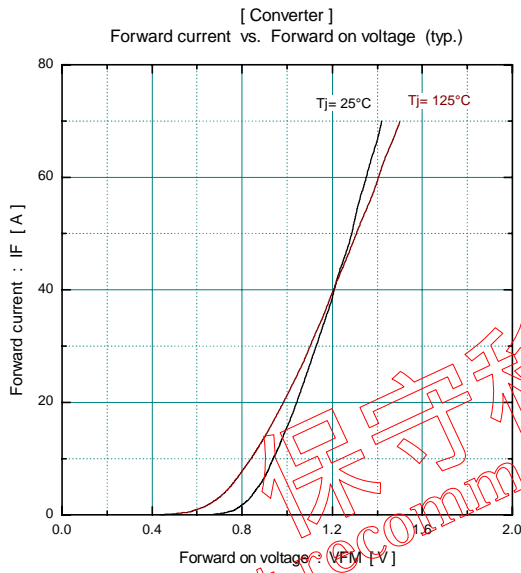
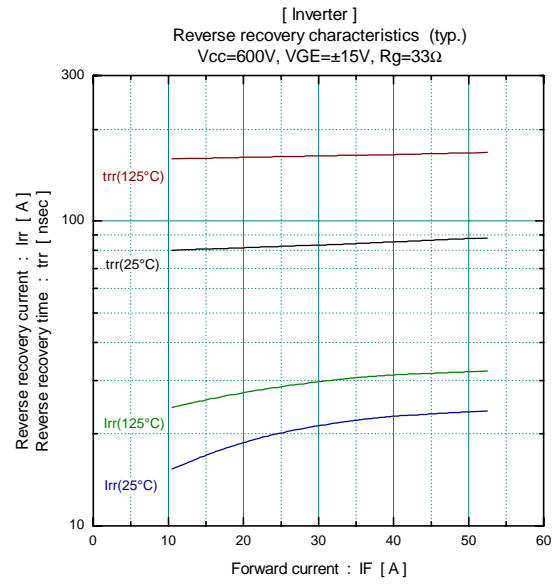
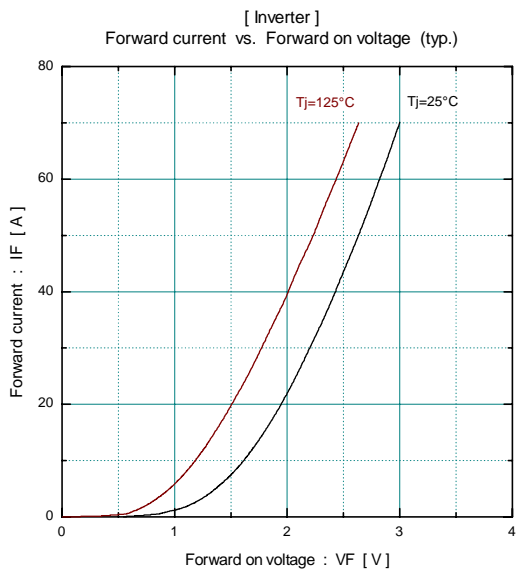
■ Characteristics (Representative)



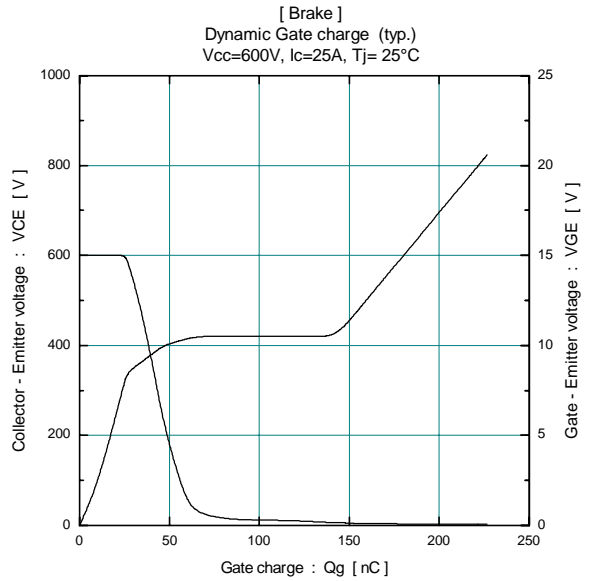
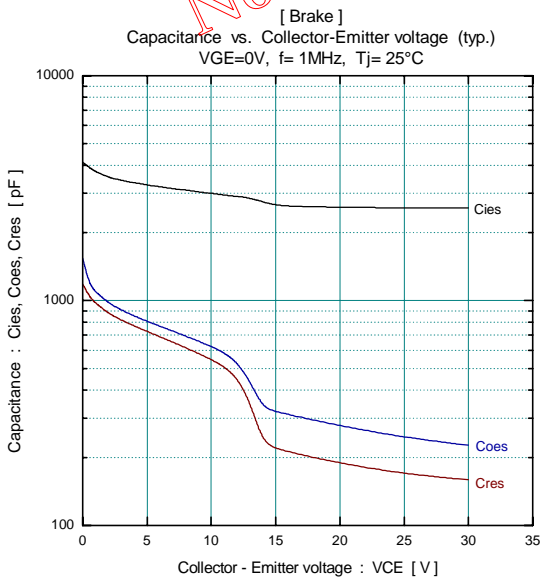
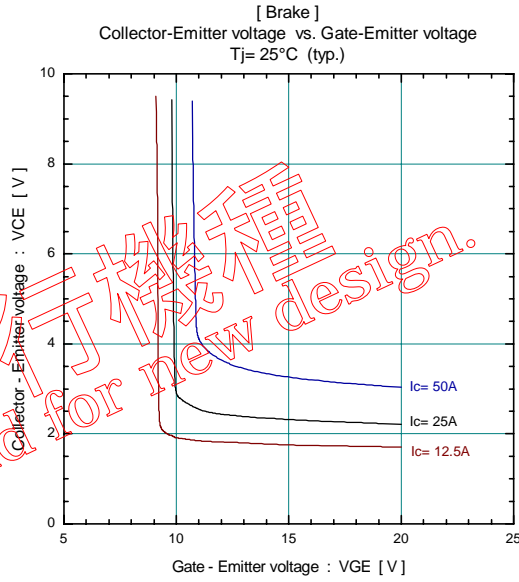
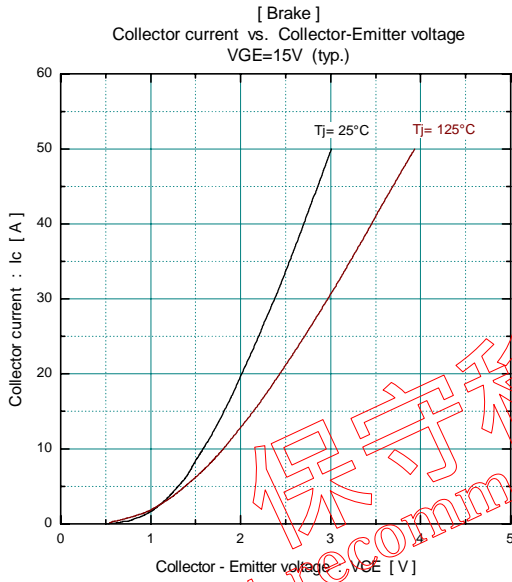
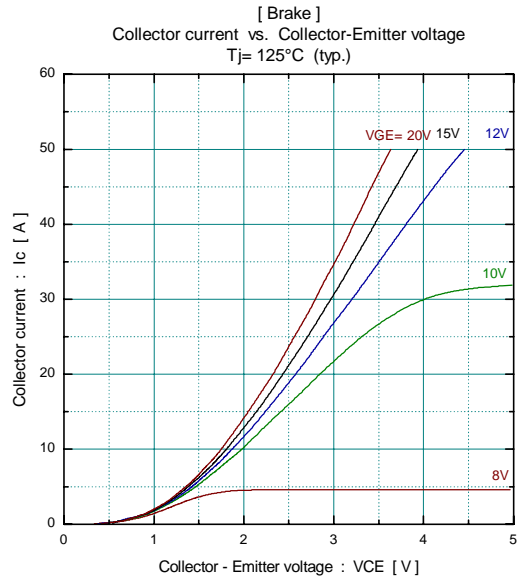
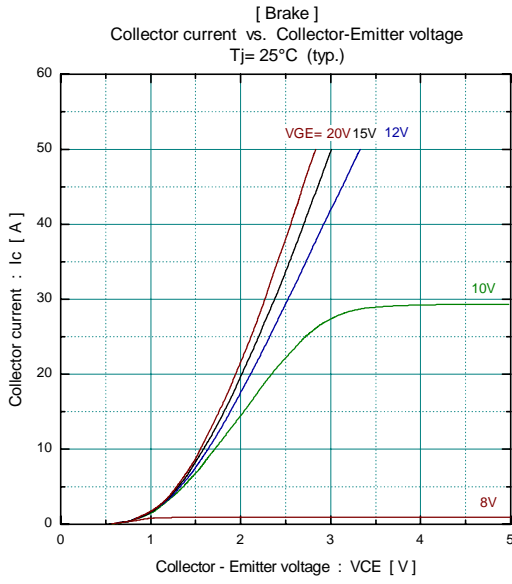
保守移行機種
Not recommended for new design.



保守移行機種
Not recommended for new design.

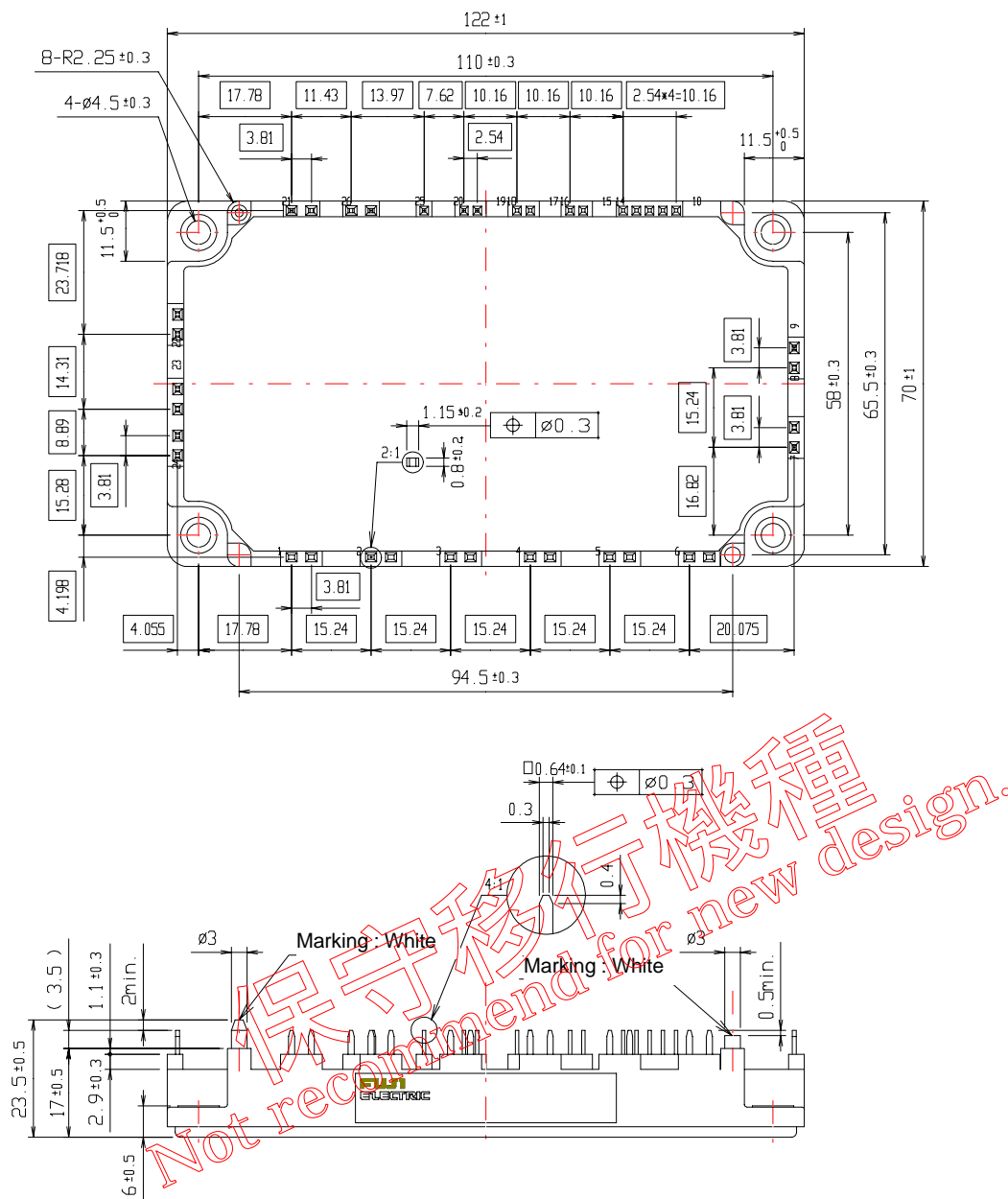


保守移行機種
Not recommend for new design.



Not recommend for new design.

■ Outline Drawings, mm



■ Equivalent Circuit Schematic

